

COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES
- MEDIUM VOLTAGE CAPABILITY
- SURFACE-MOUNTING TO-252 (DPAK) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICAL SIMILAR TO MJE340 AND MJE350

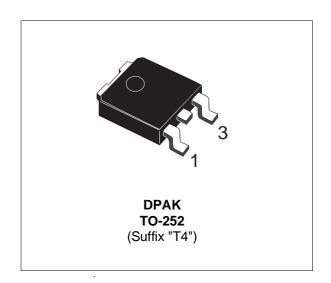
APPLICATIONS

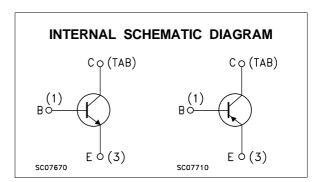
- SOLENOID/RELAY DRIVERS
- GENERAL PURPOSE SWITCHING AND AMPLIFIER

DESCRIPTION

The MJD340 and MJD350 form complementary NPN - PNP pairs.

They are manufactured using Medium Voltage Epitaxial-Planar technology, resulting in a rugged high performance cost-effective transistor.





ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit | |
|------------------|--|-------|------------|----|
| | | NPN | MJD340 | |
| | | PNP | MJD350 | |
| V _{CBO} | Collector-Base Voltage (IE = 0) | | 300 | V |
| V _{CEO} | Collector-Emitter Voltage (I _B = 0) | | 300 | V |
| V _{EBO} | Emitter-Base Voltage (IC = 0) | | 3 | V |
| Ic | Collector Current | | 0.5 | А |
| I _{CM} | Collector Peak Current (tp = 25 °C) | | 0.75 | А |
| P _{tot} | Total Power Dissipation at T _{case} ≤ 25 °C | 15 | W | |
| T _{stg} | Storage Temperature | | -65 to 150 | °C |
| Tj | Max Operating Junction Temperature | | 150 | °C |

For PNP types voltage and current values are negative.

September 2003 1/5

THERMAL DATA

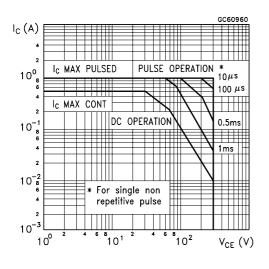
| R _{thj-case} | Thermal Resistance Junction-case | Max | 8.33 | °C/W | |
|-----------------------|-------------------------------------|-----|------|------|--|
| $R_{thj-amb}$ | Thermal Resistance Junction-ambient | Max | 100 | °C/W | |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

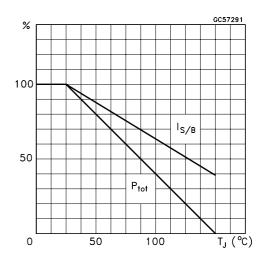
| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|-------------------------|---|---|------|------|------|------|
| I _{CBO} | Collector Cut-off Current (v _{BE} = 0) | V _{CB} = 300 V | | | 0.1 | mA |
| I _{EBO} | Emitter Cut-off Current (I _C = 0) | V _{EB} = 3 V | | | 0.1 | mA |
| V _{CEO(sus)} * | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 1 mA | 300 | | | V |
| h _{FE} * | DC Current Gain | $I_C = 50 \text{ mA}$ $V_{CE} = 10 \text{ V}$ | 30 | | 240 | |

^{*} Pulsed: Pulse duration = $300 \,\mu s$, duty cycle $\leq 2 \,\%$ For PNP type voltage and current values are negative.

Safe Operating Area

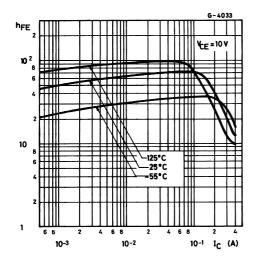


Derating Curve

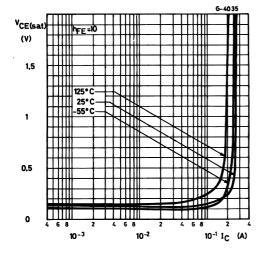


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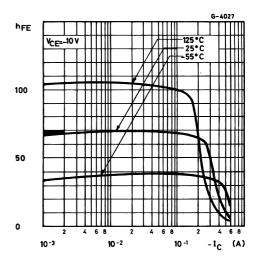
DC Current Gain (NPN type)



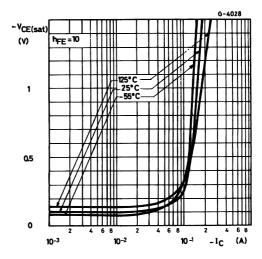
Collector Emitter Saturation Voltage (NPN type)



DC Current Gain (PNP type)

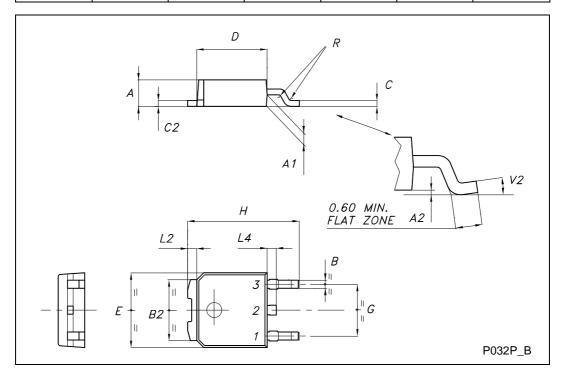


Collector Emitter Saturation Voltage (PNP type)



| TO-252 | (DPAK) | MECHANICAL | DATA |
|---------|---------|-------------------|---------------------------------|
| I O-ZJZ | IDI AIN | MILCHAINCAL | ν α ι α |

| DIM. | mm | | | inch | | | |
|------|------|------|-------|-------|-------|-------|--|
| J.W. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | |
| А | 2.20 | | 2.40 | 0.087 | | 0.094 | |
| A1 | 0.90 | | 1.10 | 0.035 | | 0.043 | |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 | |
| В | 0.64 | | 0.90 | 0.025 | | 0.035 | |
| B2 | 5.20 | | 5.40 | 0.204 | | 0.213 | |
| С | 0.45 | | 0.60 | 0.018 | | 0.024 | |
| C2 | 0.48 | | 0.60 | 0.019 | | 0.024 | |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 | |
| E | 6.40 | | 6.60 | 0.252 | | 0.260 | |
| G | 4.40 | | 4.60 | 0.173 | | 0.181 | |
| Н | 9.35 | | 10.10 | 0.368 | | 0.398 | |
| L2 | | 0.8 | | | 0.031 | | |
| L4 | 0.60 | | 1.00 | 0.024 | | 0.039 | |
| V2 | 0° | | 8° | 0° | | 0° | |



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